

PSMN7R6-60BS

N-channel 60 V 7.8 m Ω standard level MOSFET in D2PAK Rev. 2 — 2 March 2012 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	60	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	92	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	149	W
Tj	junction temperature		-55	-	175	°C
Static charact	eristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 13; see Figure 9	-	5.9	7.8	mΩ
Dynamic char	acteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $V_{DS} = 30 \text{ V}$; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	10.6	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $V_{DS} = 30 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	38.7	-	nC
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 92 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω ; unclamped	-	-	110	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		<u>_</u>
2	D	drain[1]	mb	D D
3	S	source		
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN7R6-60BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	60	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	60	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	65	Α
		$V_{GS} = 10 \text{ V}$; $T_{mb} = 25 \text{ °C}$; see <u>Figure 1</u>	-	92	Α
I_{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; see Figure 3	-	389	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	149	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drai	in diode				
Is	source current	T _{mb} = 25 °C	-	92	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	389	Α
Avalanche i	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 92 A; $V_{sup} \le$ 100 V; R_{GS} = 50 Ω ; unclamped	-	110	mJ

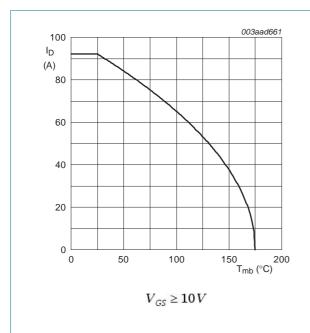


Fig 1. Continuous drain current as a function of mounting base temperature

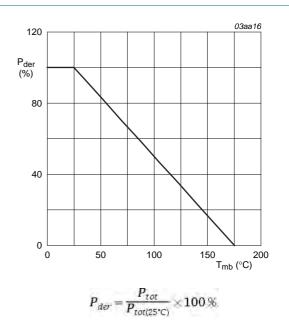
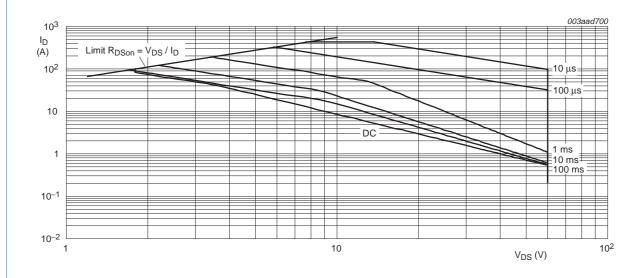


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25 \, {}^{\circ}C; I_{DM}$ is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.49	1.01	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

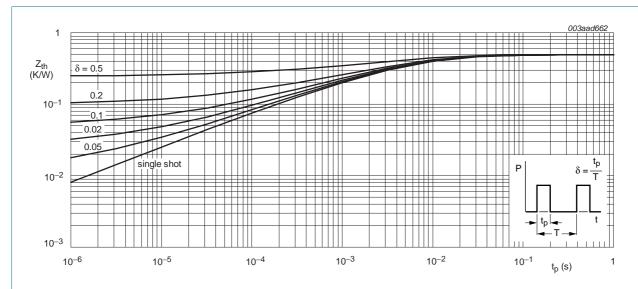


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

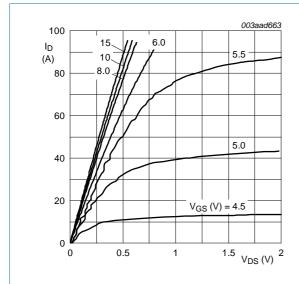
Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
V_{GSth}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; see <u>Figure 11</u>	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 11</u>	-	-	4.6	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R _{DSon} drain-source on- resistance	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12	-	13.3	18	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13; see Figure 9	-	5.9	7.8	mΩ
R _G	gate resistance	f = 1 MHz	-	0.98	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	38.7	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	12.9	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	6.9	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	6	-	nC
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}$; $V_{DS} = 30 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	10.6	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 30 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5.6	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 16}}{\text{Figure 8}}$	-	2651	-	pF
C _{oss}	output capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{}$	-	342	-	pF
C _{rss}	reverse transfer capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 16}}{\text{Figure 8}}$	-	183	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	19	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	21	-	ns
t _{d(off)}	turn-off delay time		-	37	-	ns
t _f	fall time		-	13	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.86	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 30 \text{ V}$	-	40.4	-	ns
Q _r	recovered charge		-	56	-	nC



 $T_i = 25$ °C; $t_p = 300 \, \mu s$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

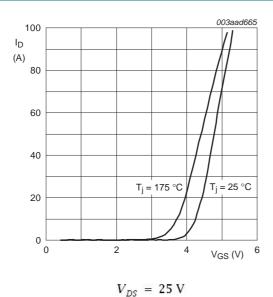


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

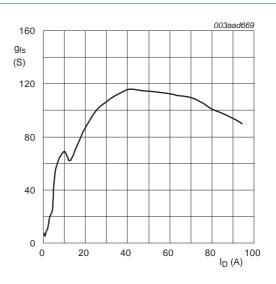
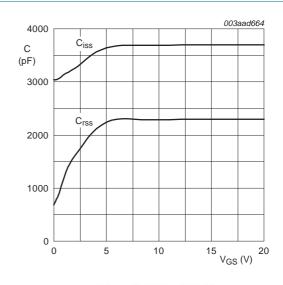


Fig 6. Forward transconductance as a function of drain current; typical values



 $V_{DS} = 0 \text{ V; } f = 1 \text{ MHz}$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

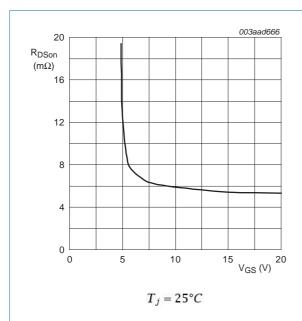
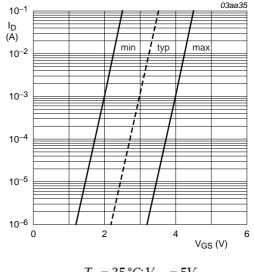


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

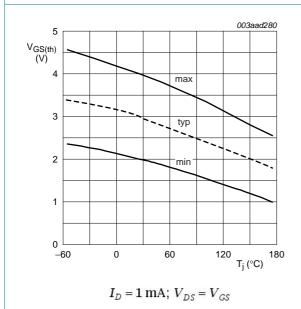


Fig 11. Gate-source threshold voltage as a function of junction temperature

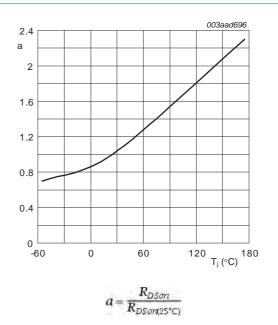


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

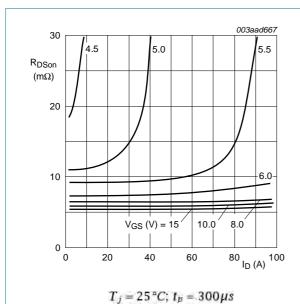
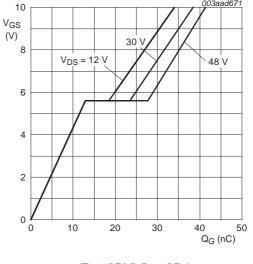


Fig 13. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25^{\circ}C; I_D = 25 A$

Fig 14. Gate-source voltage as a function of gate charge; typical values

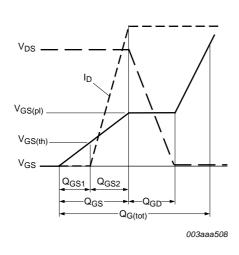
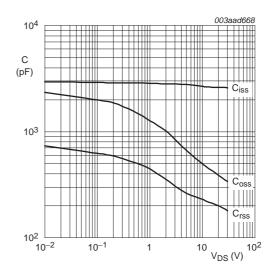


Fig 15. Gate charge waveform definitions



 $V_{DS} = 0V$; f = 1 MHz

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

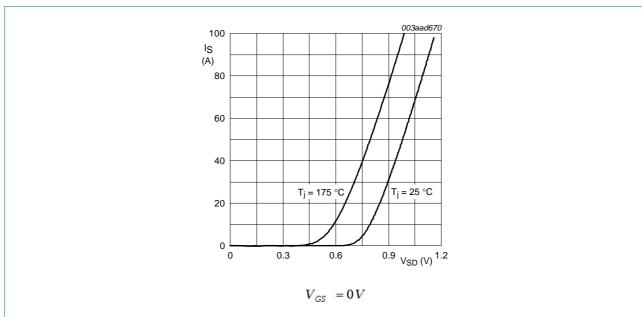


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

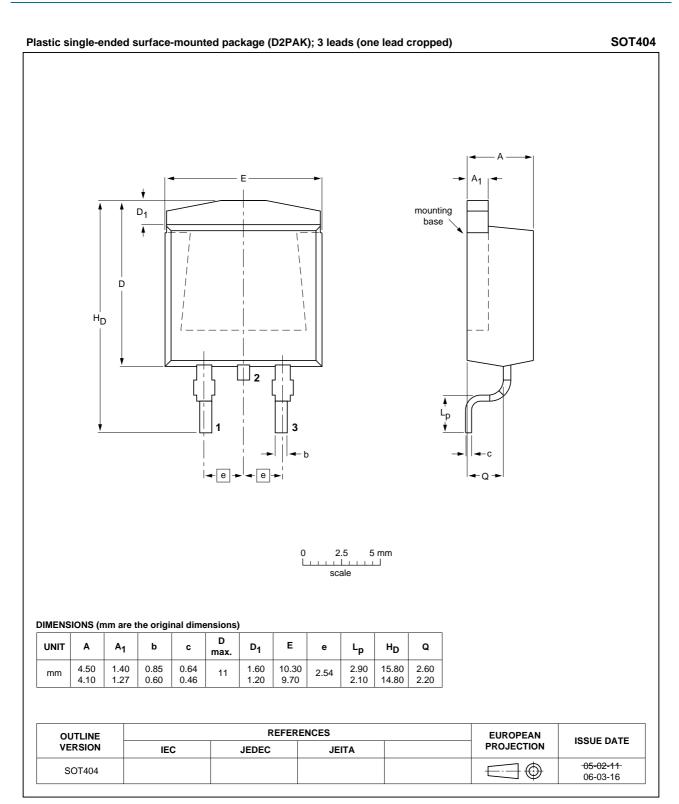


Fig 18. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R6-60BS v.2	20120302	Product data sheet	-	PSMN7R6-60BS v.1
Modifications:	Status changedVarious changes	from objective to product. s to content.		
PSMN7R6-60BS v.1	20111020	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PSMN7R6-60BS

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PSMN7R6-60BS

N-channel 60 V 7.8 mΩ standard level MOSFET in D2PAK

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PSMN7R6-60BS

Nexperia

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